

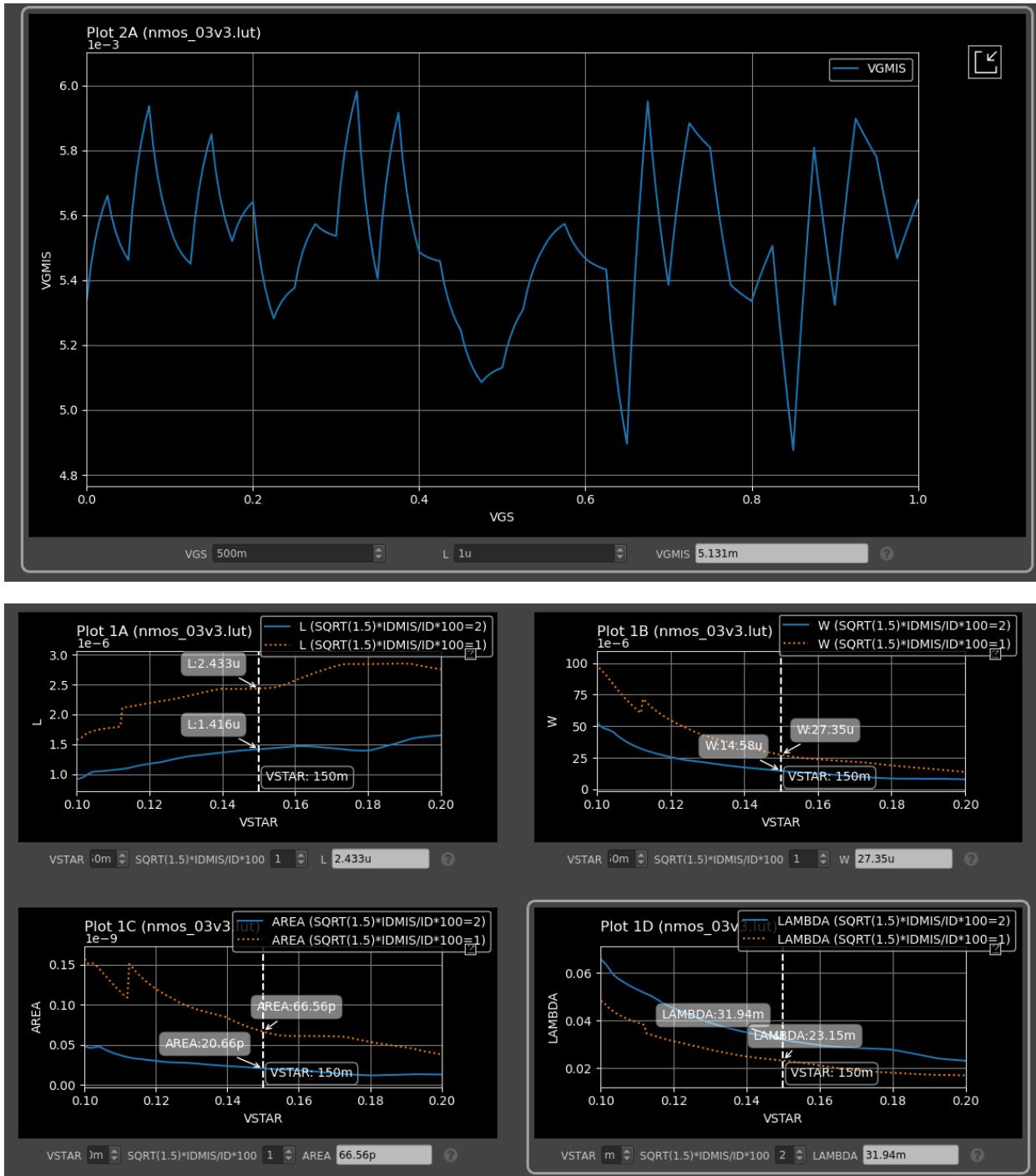
ITI
LAB 5

Simple vs Wide Swing (Low Compliance)
Cascode Current Mirror

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Part 1: Exploring Sizing Tradeoffs Using SA



From the above graphs $W = 14.58 \mu m$, $L = 1.416 \mu m$

```

sm141064.ngspice
~/pdk/gf180mcuC/libs.tech/ngspice
734 ****
735 * 3.3V NMOS Models
736 ****
737 *
738 .lib nmos_3p3_t
739
740
741 .subckt nmos_3p3_sab d g s b w=10u l=0.28u par=1 s_sab=0.48u d_sab=1.78u as=0 ad=0 ps=0 pd=0 nrd=0 nrs=0 dttemp=0 nf=1 sa=0 sb=0 sd=0 m=1
742
743 .param
744 + par_vth=0.007148
745 + par_k=0.007008
746 + par_leff=1.5e-7
747 + par_weff=1
748 + par_leff='l*par_l'
749 + par_weff='par_w*par_w'
750 + p_sqrtarea='sqrt((par_leff)*(par_weff))'
751 param
752 + var_k='0.7071*par_k* 1e-06 / p_sqrtarea'
753 + mis_k=gauss(0,var_k,1)
754
755
756 .param
757 + var_vth='0.7071*par_vth* 1e-06 / p_sqrtarea'
758 + mis_vth=gauss(0,var_vth,1)
759
760 xr1 d1 b nplus_u_m1 wr='w' lr='(d_sab==0) ? 1e-15 : d_sab'
761 xr2 s s1 b nplus_u_m1 wr='w' lr='(s_sab==0) ? 1e-15 : s_sab'
762
763
764 m1 d1 g s1 b nmos_3p3 w='w' l='l' as=as ad=ad ps=ps pd=pd nrd=nrd nrs=nrs nf=nf sa=sa sb=sb sd=sd
765 +delvto='mis_vth*sw_stat_mismatch'
766 .ends
767
768
769 .model nmos_3p3.0 nmos
770 level = 54
771 +lmin = 2.0e-007
772 +lmax = 5e-007
773 +wmin = 2.2e-007
774 +wmax = 5e-007
775 +version = 4.5
776 +blnunit = 2
777 +naramchka = 1

```

$L=1\mu m$ $W=1\mu m$

$$L_{eff} = L - par_{leff} \quad L_{eff} = 8.5 \times 10^{-7}$$

$$W_{eff} = par(W - par_w) \quad W_{eff} = 1.1 \times 10^{-6}$$

$$p_{sqerarea} = \sqrt{par_{leff} \times par_{weff}}$$

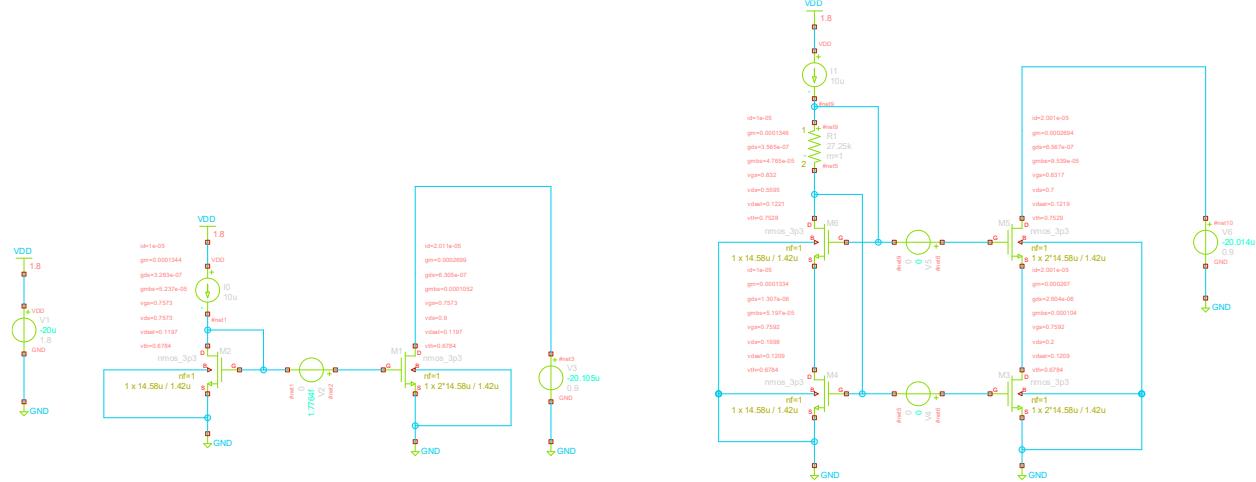
$$p_{sqerarea} = 9.67 \times 10^{-7}$$

$$VGMIS = \frac{0.7071 \times par_{vth} \times 1 \times 10^{-6}}{p_{sqerarea}}$$

$$VGMIS = 5.23mV$$

Part 2: Current Mirror Simulation

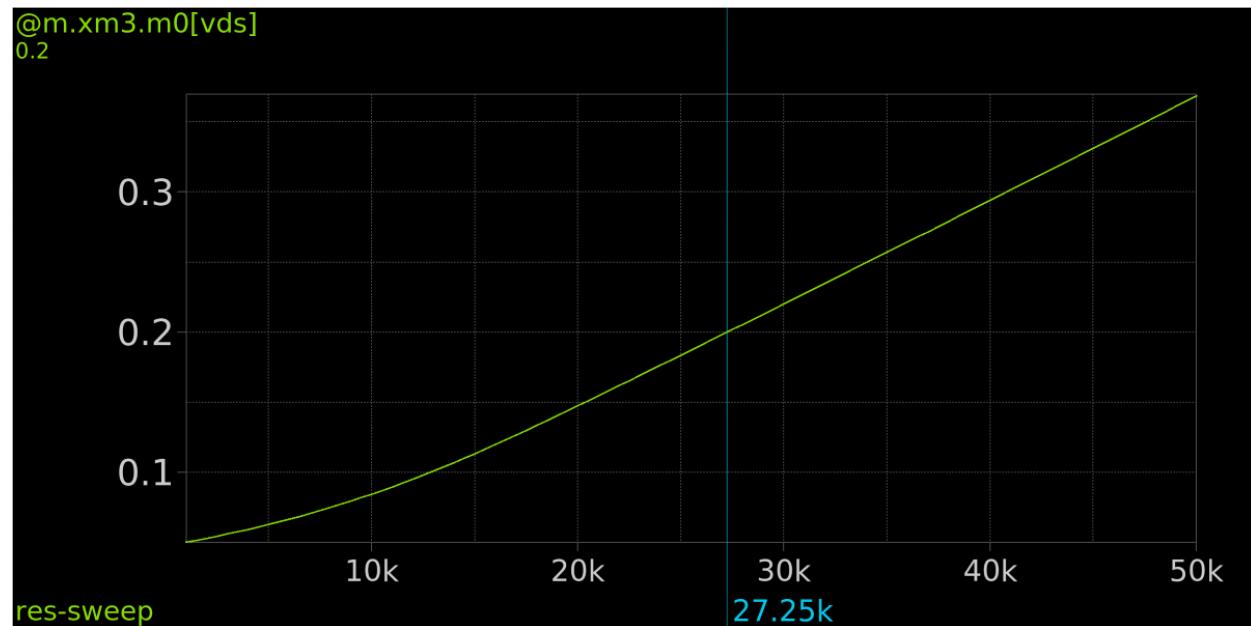
Schematic



R_B calculation

Since $R_B = \frac{V_{DS3}}{I_B}$, $V_{DS3} = V^* + 50mV$, $V^* = 150mV$

$$R_B = 20K\Omega$$

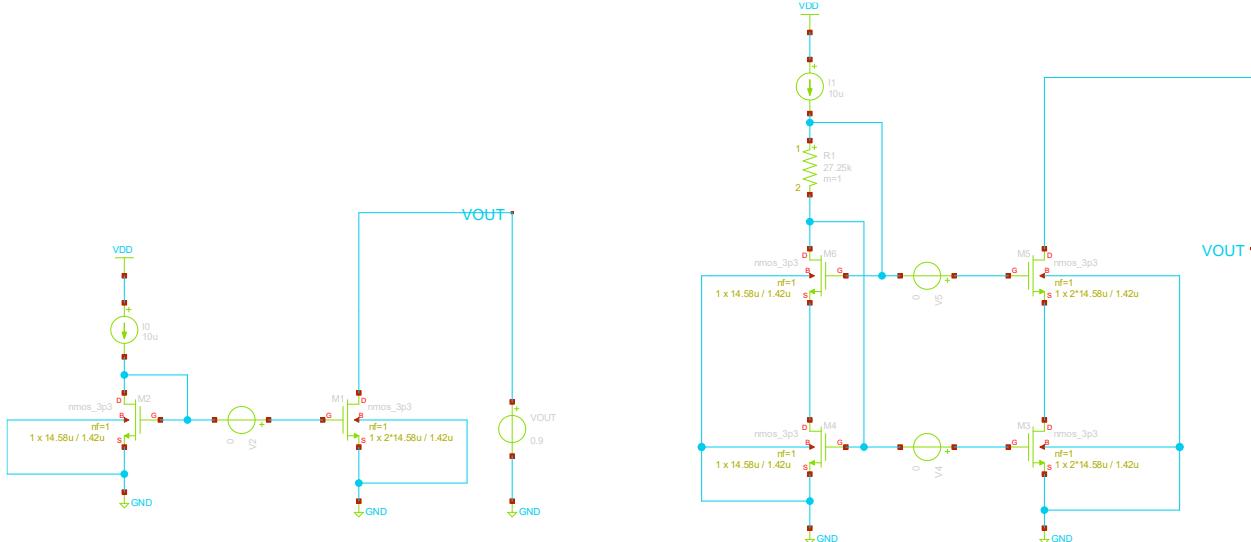


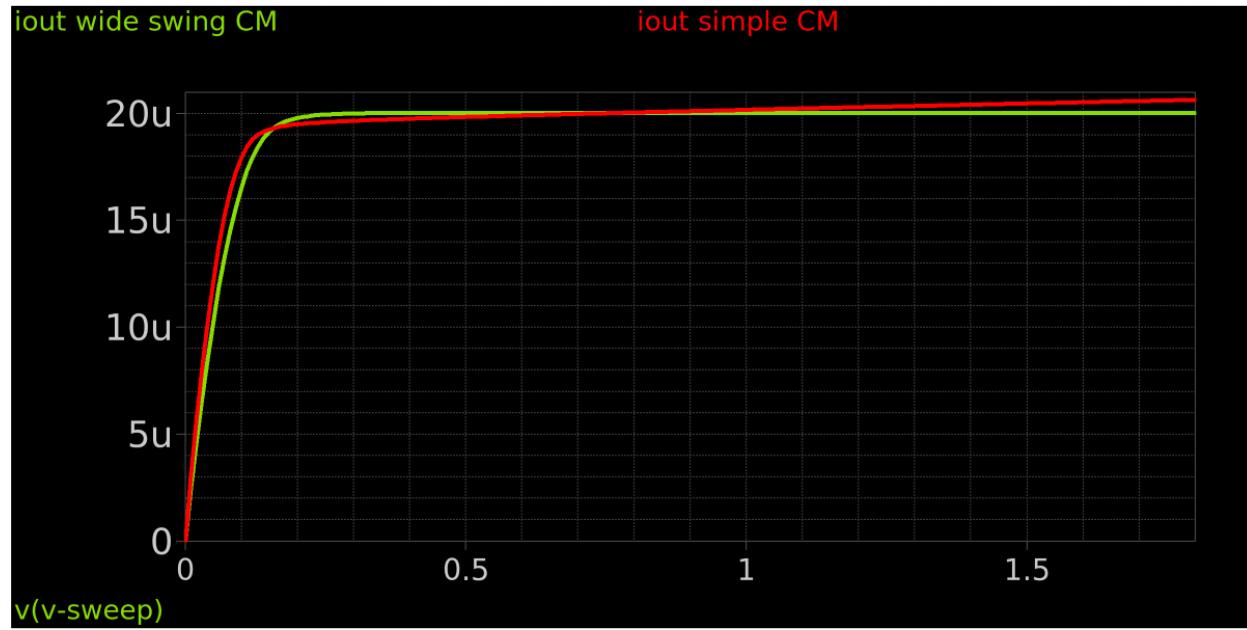
From the graph the value of $R_B = 27.25K\Omega$

Comment: The simulated value of R_B is larger than the analytical value. This discrepancy is expected because the analytical calculation typically involves simplifying ,while In contrast, the simulation considers more accurate transistor models and mismatch effects, which often result in a higher R_B to meet the same performance targets.

Transistor	Vds	Vdsat	Region
M1	0.9	0.7573	Saturation
M2	0.7573	0.1197	Saturation
M3	0.2	0.1209	Saturation
M4	0.1998	0.1209	Saturation
M5	0.7	0.1219	Saturation
M6	0.5595	0.1121	Saturation

DC Sweep (I_{out} vs VOUT)

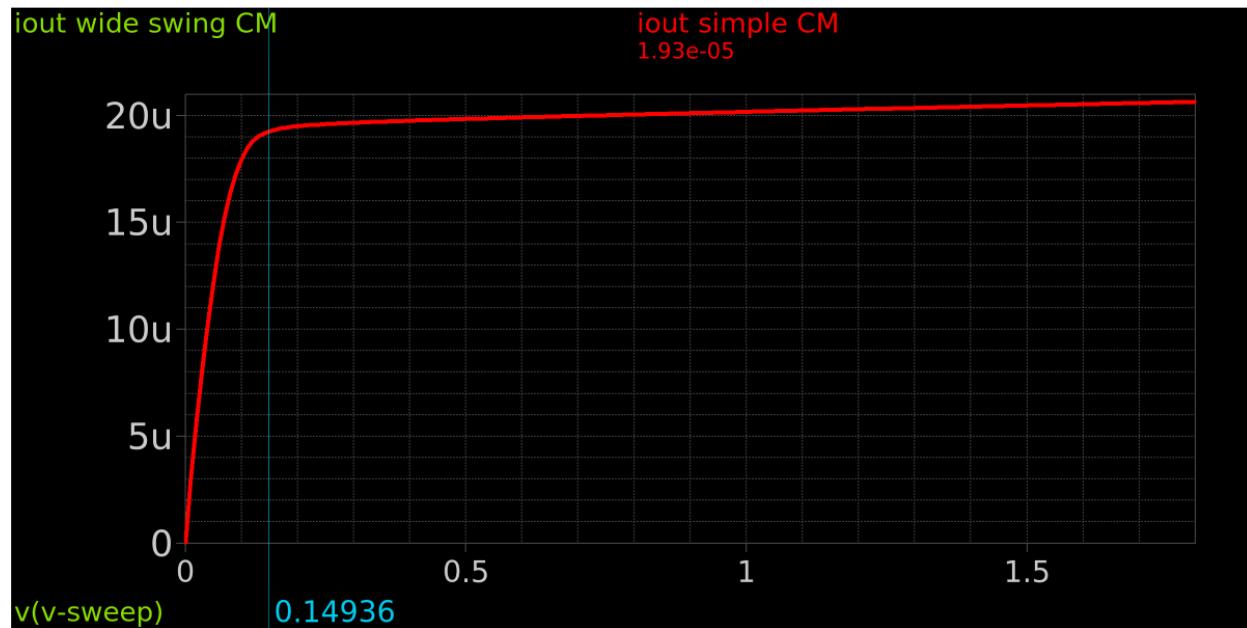


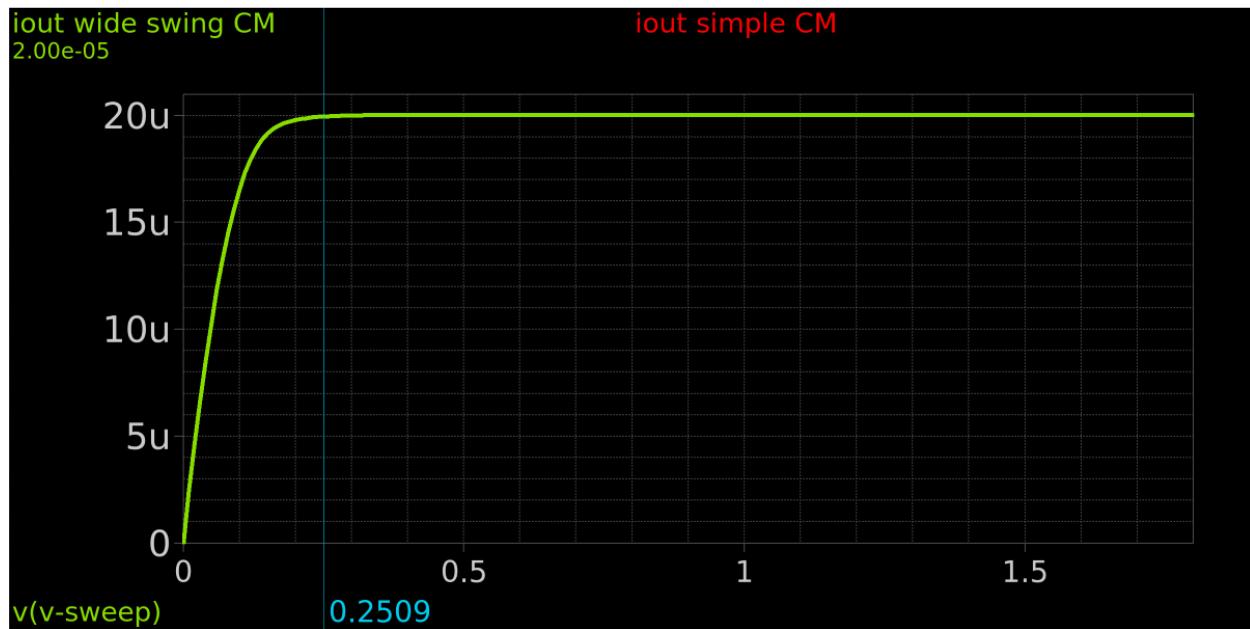


Comment:

When comparing the I_{out} vs. V_{out} characteristics of the simple current and the wide swing CM, we observe that in the simple CM, I_{out} continues to increase approximately linearly with V_{out} beyond a certain point. This indicates poor output resistance and weak current regulation.

In contrast, the wide swing CM shows that I_{out} becomes constant after a certain V_{out} , reflecting much better current regulation and higher output resistance. This behavior is due to the cascode structure maintaining the output transistor in saturation over a wider voltage range, thereby achieving improved output characteristics.





From the above 2 graphs,

$$V_{compliance}(\text{Simple CM}) = 0.15V$$

$$V_{compliance}(\text{Wide swing CM}) = 0.251V$$

5.000000e-01	1.983372e-05	1.500000e+00	2.046570e-05
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Figure 1 Iout at Vds=0.5V

Figure 2 Iout at Vds=1.5V

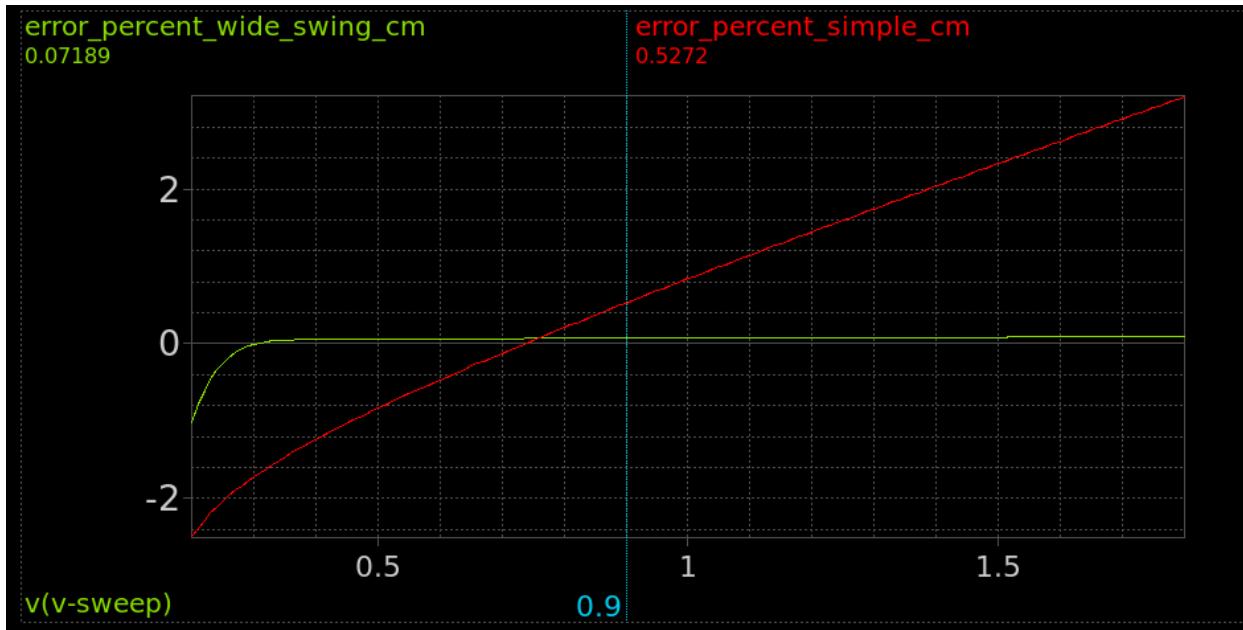
$$\Delta I = \frac{2.0465 - 1.9833}{2} \times 100$$

$$\Delta I = 3.16\%$$

7.400000e-01	2.000230e-05
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Figure 3 Vds at Iout=2IB

$I_{out} = 2 I_B$ at $V_{out} = 0.74V$ which is V_{ds} of the transistor



Comment: The error percentage between I_B and I_{out} is noticeably higher in the Simple Current Mirror, particularly at higher output voltages. This is primarily due to the limited output resistance and reduced compliance range, which causes I_{out} to deviate more significantly from the bias current as V_{out} increases.

In contrast, the Wide-Swing Current Mirror demonstrates significantly lower error percentages across a wider range of V_{out} . This improvement is due to its enhanced output impedance and increased output voltage swing capability, which allows it to better maintain I_{out} close to the bias current.



- Comment: The output resistance R_{out} of the Wide-Swing Current Mirror is significantly higher than that of the Simple Current Mirror. This is evident from the flatter I_{out} vs. V_{out} characteristic in the wide-swing design, indicating better current source behavior. In the Simple CM, R_{out} is limited by the intrinsic output resistance of a single MOSFET, resulting in a noticeable slope in the I_{out} vs. V_{out} curve. On the other hand, the Wide-Swing CM uses a cascode-like configuration that improves the output impedance by reducing the effect of V_{out} on the current. This leads to a more constant I_{out} , especially at higher V_{out} , and confirms that the wide-swing mirror offers superior performance in terms of output resistance.
- In both the simple and wide-swing current mirror topologies, R_{out} initially varies with V_{out} , but then becomes approximately constant beyond a certain V_{out} level. This behavior suggests that at lower output voltages, the transistors are transitioning between regions which affects output resistance. As V_{out} increases and the transistors settle into the saturation region, R_{out} stabilizes and becomes nearly independent of V_{out} .

Analytically Calculating the value of R_{out}

- R_{out} of the simple current mirror

$$R_{out} = \frac{1}{g_{ds1}}, g_{ds1} = 6.305 \times 10^{-7}$$

$$R_{out} = 1.58M\Omega$$

b) R_{out} of the wide swing CM

$$R_{out} = r_{o5}(1 + (g_{m5} + g_{mb5}) r_{o3}),$$

$$g_{ds5} = 6.578 \times 10^{-7}, g_{m5} = 2.694 \times 10^{-4}, g_{mb5} = 9.539 \times 10^{-5},$$

$$g_{ds3} = 2.6041 \times 10^{-6}$$

$$R_{out} = 2.145 \times 10^8 \Omega$$

Mismatch

Calculating the value of the range of VMIS

VMIS will be swept from 0 to $\frac{\sqrt{1.5 \times 3.5} \times 10^{-3}}{\sqrt{W \times L} \times 10^{12}}$, $W = 14.58 \mu m$, $L = 1.416 \mu m$

then VMIS will be swept from 0 to 942mV

1. Sweeping VMIS1 and making VMIS2=0

Monitoring the change of Iout of the simple CM

0.000000e+00	2.010544e-05	9.400000e-04	2.036020e-05
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The percent of change in $I = \frac{|I_0 - I|}{I_0} \times 100$

Change=1.25%

Monitoring the change of Iout of the wide swing CM

0.000000e+00	2.001438e-05	9.400000e-04	2.026462e-05
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The percent of change in $I = \frac{|I_0 - I|}{I_0} \times 100$

Change=1.25%

2. Sweeping VMIS2 and making VMIS1=0

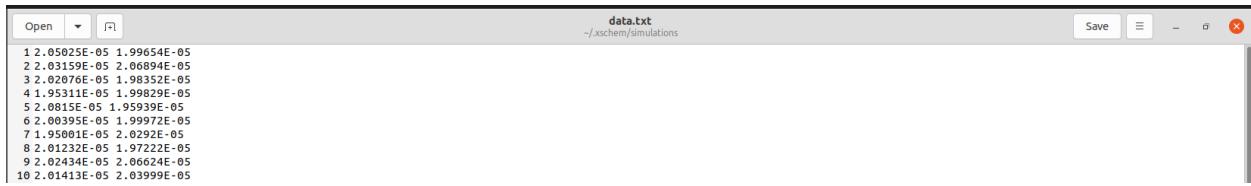
Monitoring the change of Iout of the wide swing CM

0.000000e+00	2.001438e-05	9.400000e-04	2.001616e-05
--------------	--------------	--------------	--------------

$$\text{The percent of change in } I = \frac{|I|_0 - |I|_{vgmis}}{|I|_0} \times 100$$

$$\text{Change} = 8.89 \times 10^{-3} \%$$

Monte Carlo (MC) Simulation



MATLAB code

```
% Load the data from text file
data = load('data.txt');

% Separate the two columns
col1 = data(:,1);
col2 = data(:,2);

% Binwidth
binwidth = 5e-8;

% Compute mean and standard deviation
mean1 = mean(col1);
std1 = std(col1);
std_percent1 = (std1 / mean1) * 100;

mean2 = mean(col2);
std2 = std(col2);
std_percent2 = (std2 / mean2) * 100;

% Create histograms with Gaussian fits
figure;

subplot(2,1,1);
histogram(col1, 'Binwidth', binwidth, 'Normalization', 'pdf');
hold on;
x1 = linspace(min(col1), max(col1), 1000);
y1 = normpdf(x1, mean1, std1);
plot(x1, y1, 'r', 'LineWidth', 1.5);
title(sprintf('Iout of the simple CM (Std Dev = %.3f%%)', std_percent1));
xlabel('value');
ylabel('Probability Density');
```

```

subplot(2,1,2);
histogram(col2, 'Binwidth', binwidth, 'Normalization', 'pdf');
hold on;
x2 = linspace(min(col2), max(col2), 1000);
y2 = normpdf(x2, mean2, std2);
plot(x2, y2, 'r', 'LineWidth', 1.5);
title(sprintf('Iout of the wide swing CM (Std Dev = %.3f%%)', std_percent2));
xlabel('value');
ylabel('Probability Density');

```

